

30V N-channel SGT MOSFET

DESCRIPTION

The CX3400 uses advanced trench technology to provide excellent $R_{D(ON)}$ and low gate charge.

This device is suitable for use as a load switch or in PWM applications.

Product Summary

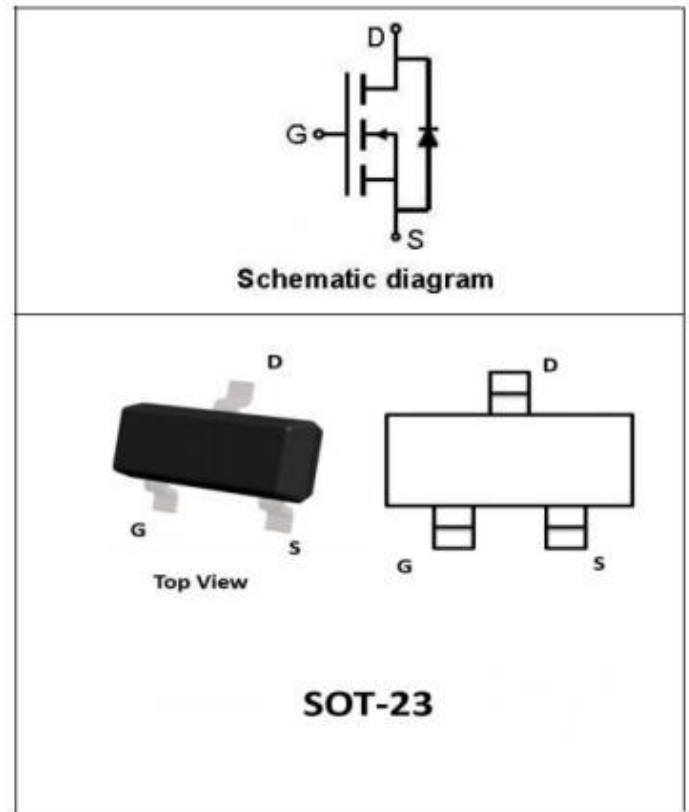
- $R_{D(ON)} < 30m\Omega$ @ $V_{GS}=10V$
- $R_{D(ON)} < 40m\Omega$ @ $V_{GS}=4.5V$

GENERAL FEATURES

- Trench Power LV MOSFET technology
- High density cell design for low $R_{D(ON)}$
- High Speeds switching

Application

- Battery protection
- Load switch
- Power management



■ Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	30	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_C=25^{\circ}C$	I_D	5.6	A
	$T_C=75^{\circ}C$		4.5	
Pulsed Drain Current ^A		I_{DM}	30	A
Total Power Dissipation	$T_C=25^{\circ}C$	P_D	1.2	W
	$T_C=70^{\circ}C$		0.9	
Thermal Resistance Junction-to-Ambient @ Steady State ^B		$R_{\theta JC}$	105	$^{\circ}C/W$
Junction and Storage Temperature Range		T_J, T_{STG}	$-55 \sim +150$	$^{\circ}C$